

20V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 10)
20V	$4.6 m\Omega$ @ $V_{GS} = 4.5 V$	50A
20 V	$8.7 \text{m}\Omega$ @ $V_{GS} = 2.5 \text{V}$	36A

Features and Benefits

- Low R_{DS(ON)}—Ensures On-State Losses are Minimized
- Small-Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching, Test in Production— Ensures More Reliable And Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

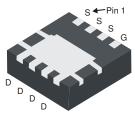
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Motor Control
- Load Switch
- DC-DC Converters

Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.072 grams (Approximate)

PowerDI3333-8





Equivalent Circuit

Bottom View

Top View

Ordering Information (Note 5)

Part Number	Case	Packaging		
DMN2005UFGQ-7	PowerDI3333-8	2000/Tape & Reel		
DMN2005UFGQ-13	PowerDI3333-8	3000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



N05= Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)

Document number: DS41561 Rev. 4 - 2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	20	V		
Gate-Source Voltage	V _{GSS}	±12	V		
Continuous Dusin Compant (Natos 79.10) V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	50 40	А
Continuous Drain Current (Notes 7&10) V _{GS} = 4.5V		$T_A = +25$ °C $T_A = +70$ °C	I _D	18 14	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	130	Α		
Maximum Continuous Body Diode Forward Current (I	Is	2.6	Α		
Avalanche Current , L = 0.2mH	I _{AS}	23.9	Α		
Repetitive Avalanche Energy, L = 0.2mH	E _{AS}	58.4	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	T _A = +25°C	P_{D}	1.05	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{OJA}	120	°C/W
Total Power Dissipation (Note 7)		P _D	2.27	W
Thermal Resistance, Junction to Ambient (Note 7) Steady State		R _{OJA}	55	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{OJC}	6.1	- C/VV
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C	

Notes:

- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

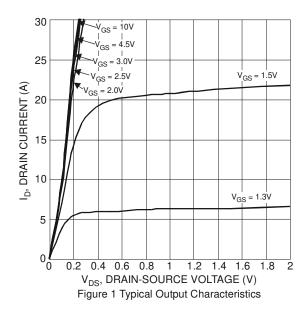


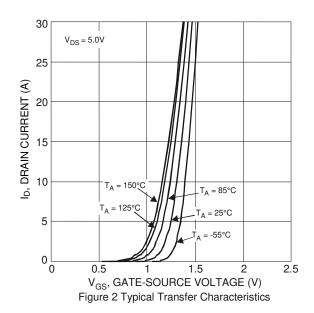
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_		٧	$V_{GS} = 0V$, $I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	10	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.4	0.7	1.2	٧	$V_{DS} = V_{GS}, \ I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	4	4.6	mΩ	$V_{GS} = 4.5V, I_D = 13.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	4.9	8.7		V _{GS} = 2.5V, I _D = 13.5A	
Diode Forward Voltage	V_{SD}	_	0.8	1.1	V	$V_{GS} = 0V, I_{S} = 27A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	6,495	1	pF		
Output Capacitance	Coss	_	546	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	477	_	pF	11 = 11VIITZ	
Gate Resistance	Rg	_	0.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	68.8	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	164	_	nC	1011 074	
Gate-Source Charge	Q_{gs}	_	10.4	_	nC	$V_{DS} = 16V, I_D = 27A$	
Gate-Drain Charge	Q_{gd}	_	17.4	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	12.4	_	ns	$V_{GS} = 5V, V_{DS} = 10V,$ $R_{G} = 4.7\Omega, I_{D} = 13.5A$	
Turn-On Rise Time	t _R	_	25.7	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	114	_	ns		
Turn-Off Fall Time	t _F	_	38	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	16.1		ns	I _F = 13.5A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	8.5	_	nC	I _F = 13.5A, di/dt = 100A/μs	

Notes:

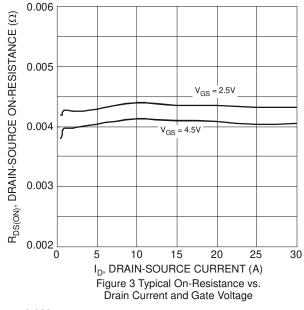
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.
- 10. Limited by package.

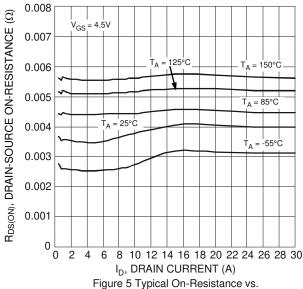


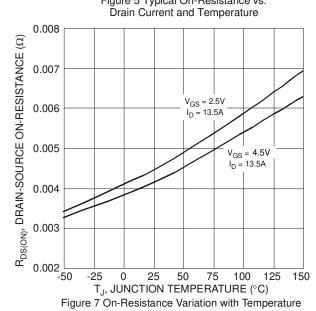


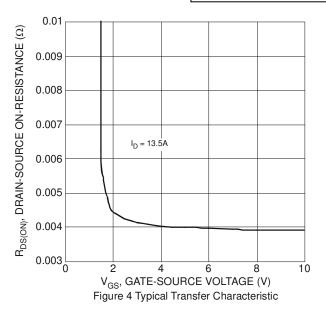












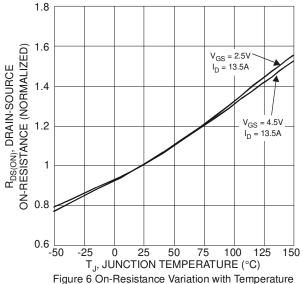
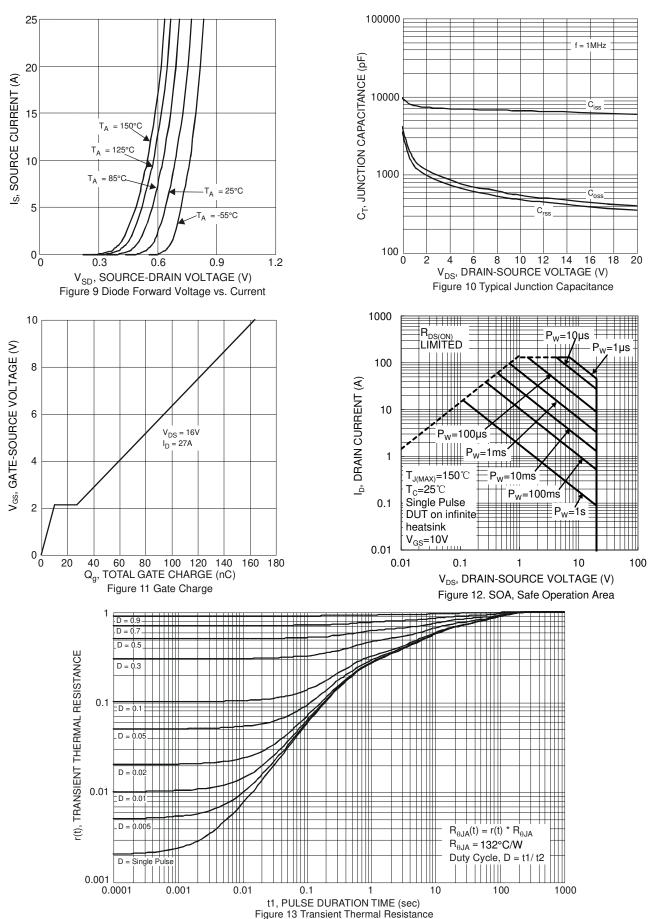


Figure 8 Gate Threshold Variation vs. Junction Temperature





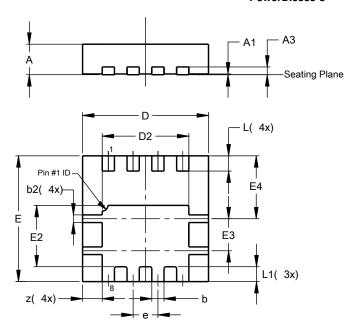




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

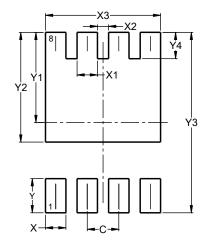


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	_	-	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
V4	0.540



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